

Digital Transistors (Built-in Resistors)

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DESCRIPTION

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SOT-723 package which is designed for low power surface mount applications.

The DTC144EM ~ DTC144TM are available in SOT-723 package

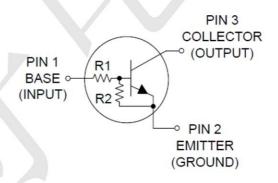
FEATURES

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SOT-723 Package can be Soldered using Wave or Reflow.
- Available in 4 mm, 8000 Unit Tape & Reel
- Available in SOT-723 package

ORDERING INFORMATION

Package Type	Part Number			
	DTC114EM			
	DTC124EM			
	DTC144EM			
	DTC114YM			
	DTC114TM			
	DTC143TM			
COT 700	DTC123EM			
SOT-723	DTC143EM			
	DTC143ZM			
	DTC124XM			
	DTC123JM			
	DTC115EM			
	DTC144WM			
	DTC144TM			
Note	SPQ: 8,000Pcs/Reel			
AiT provides all RoHS Compliant Products				

PIN DESCRIPTION





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ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted

V _{CBO} , Collector-Base Voltage	50Vdc
V _{CEO} , Collector-Emitter Voltage	50Vdc
Ic, Collector Current	100mAdc

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Total Device Dissipation		260 ^{NOTE1}	mW
T _A = 25°C Derate above 25°C	P _D	600NOTE2 2.0NOTE1 4.8 NOTE2	mW/°C
Thermal Resistance – Junction-to-Ambient	Reja	480NOTE1 205NOTE2	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{STG}	−55 to +150	°C

NOTE1: FR-4 @ Minimum Pad NOTE2: FR-4 @ 1.0 x 1.0 inch Pad



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ELECTRICAL CHARACTERISTICS

T_A = 25°C, unless otherwise noted

T _A = 25°C, unless otherwise noted Parameter	Symbol	Cond	itions	Min.	Тур.	Max.	Unit
OFF CHARACTERISTICS	Cymbo.	Containente			. , p.	7	0
Collector-Base Cutoff Current	Ісво	V _{CB} = 50V, I _E = 0		-	- /	100	nAdc
Collector-Emitter Cutoff Current	Iceo	V _{CE} = 50V, I _B =	= 0	1-1	_/	500	nAdc
Emitter-Base Cutoff Current	Ієво	V _{EB} = 6.0V, I _C = 0	DTC114EM DTC124EM DTC144EM DTC114YM DTC114TM DTC1143TM DTC123EM DTC143ZM DTC143ZM DTC123JM DTC123JM DTC115EM DTC144WM DTC144TM			0.5 0.2 0.1 0.2 0.9 1.9 2.3 1.5 0.18 0.13 0.2 0.05 0.13	mAdc
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C = 10μA, I _E =	I _C = 10μA, I _E = 0		-	-	Vdc
Collector-Emitter Breakdown VoltageNOTE3	V _{(BR)CEO}	I _C = 2.0mA, I _B	= 0	50	-	÷	Vdc
ON CHARACTERISTICSNOTE3							
	1		DTC114EM	35	60	Ċ.	
			DTC124EM	60	100		
			DTC144EM	80	140		
			DTC114YM	80	140		
			DTC114TM	160	350		
			DTC143TM	160	350		
DC Comment Code		V _{CE} =10V,	DTC123EM	8.0	15		
DC Current Gain	h _{FE}	Ic=5.0mA	DTC143EM	15	30	-	-
			DTC143ZM	80	200		
			DTC124XM	80	150		
			DTC123JM	80	140		
			DTC115EM	80	150		
			DTC144WM	80	140		
			DTC144TM	160	350		



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Parameter	Symbol	Cond	itions	Min.	Тур.	Max.	Unit
		$I_C = 10mA$, $I_B = 0.3mA$					
		$I_C = 10mA$, $I_B = 5mA$	DTC123EM			7	
Collector-Emitter Saturation			DTC143TM				
Voltage	V _{CE(sat)}		DTC114TM	-	/-	0.25	Vdc
Voltage		$I_C = 10mA$,	DTC143EM				
		$I_B = 1mA$	DTC143ZM				
			DTC124XM				
			DTC144TM				
			DTC114EM			0.2	
			DTC124EM			0.2	
			DTC114YM			0.2	
		$V_{CC} = 5.0V$,	DTC114TM			0.2	
		$V_{B} = 2.5V$, $R_{L} = 1.0k\Omega$	DTC143TM			0.2	
	VoL		DTC123EM			0.2	
			DTC143EM			0.2	
			DTC143ZM			0.2	
			DTC124XM			0.2	
Output Voltage (on)			DTC123JM	- /	-	0.2	Vdc
		$V_{CC} = 5.0V$,	DTC144EM			0.2	
		$V_B = 3.5V$,	DTC144TM			0.2	
		$R_L = 1.0k\Omega$	2.0				
	<i>Y</i>	$V_{CC} = 5.0V$,					
		$V_B = 5.5V$,	DTC115EM			0.2	
		$R_L = 1.0k\Omega$					
		$V_{CC} = 5.0V$,					
		$V_B = 4.0V$,	DTC144WM			0.2	
		$R_L = 1.0k\Omega$					
			$V_{CC} = 5.0V, V_B = 0.5V,$				
		$R_L = 1.0k\Omega$					
Output Voltage (off)		V _{CC} = 5.0V,	DTC143TM	4.9	_	_	Vdc
		$V_B = 0.25V$,	DTC143ZM				
		$R_L = 1.0k\Omega$	DTC114TM				
		vice interest. Index SNBBSSASSICUSSISS	DTC144TM				



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Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
		DTC114EM	7.0	10	13		
		DTC124EM	15.4	22	28.6		
		DTC144EM	32.9	47	61.1		
		DTC114YM	7.0	10	13	3	
		DTC114TM	7.0	10	13		
		DTC143TM	3.3	4.7	6.1		
Input Resistor	R1	DTC123EM	1.5	2.2	2.9	kΩ	
Input Resistor	NI NI	DTC143EM	3.3	4.7	6.1	K12	
		DTC143ZM	3.3	4.7	6.1		
		DTC124XM	15.4	22	28.6		
		DTC123JM	1.54	2.2	2.86		
		DTC115EM	70	100	130		
		DTC144WM	32.9	47	61.1		
		DTC144TM	32.9	47	61.1		
		DTC114EM/DTC124EM/	0.8	1.0	1.2		
		DTC144EM/DTC115EM					
		DTC114YM	0.17	0.21	0.25		
		DTC143TM/DTC114TM/	/-		_		
Resistor Ratio	R ₁ /R ₂	DTC144TM					
Resistor Ratio	K1/K2	DTC123EM/DTC143EM	0.8	1.0	1.2		
		DTC143ZM	0.055	0.1	0.185		
		DTC124XM	0.38	0.47	0.56		
		DTC123JM	0.038	0.047	0.056		
		DTC144WM	1.7	2.1	2.6		
Input Voltage	V _{I(off)}	V _{cc} = 5.0V, I _o = 100μA DTC123JM	-	-	0.5	٧	
Input Voltage	V _{I(on)}	$V_0 = 0.3V$, $I_0 = 5mA$ DTC123JM	1.1	-		V	

NOTE3: Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%



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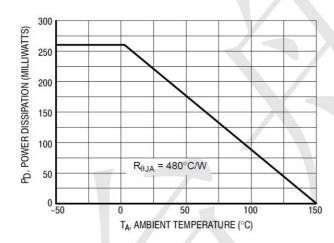
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RESISTOR VALUES

Device	R1 (k)	R2 (k)
DTC114EM	10	10
DTC124EM	22	22
DTC144EM	47	47
DTC114YM	10	47
DTC114TM	10	∞
DTC143TM	4.7	8
DTC123EM	2.2	2.2
DTC143EM	4.7	4.7
DTC143ZM	4.7	47
DTC124XM	22	47
DTC123JM	2.2	47
DTC115EM	100	100
DTC144WM	47	22
DTC144TM	47	- ∞

TYPICAL CHARACTERISTICS

Figure 1. Derating Curve





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DTC114EM

Figure 2. V_{CE(sat)} vs. I_C

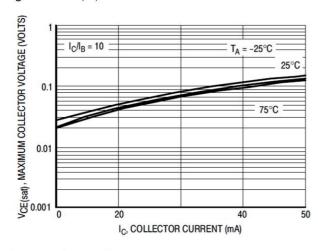


Figure 4. Output Capacitance

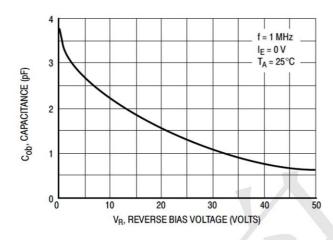


Figure 6. Input Voltage vs. Output Current

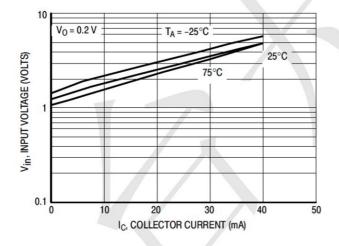


Figure 3. DC Current Gain

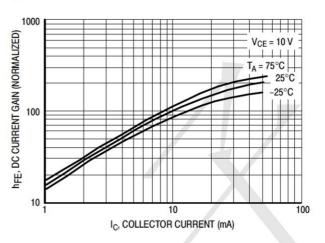
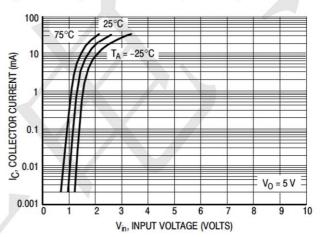


Figure 5. Output Current vs. Input Voltage





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DTC124EM

Figure 7. VCE(sat) vs. Ic

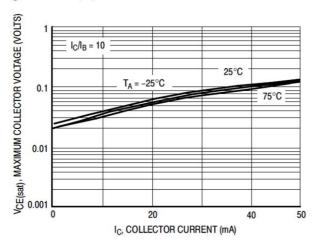


Figure 9. Output Capacitance

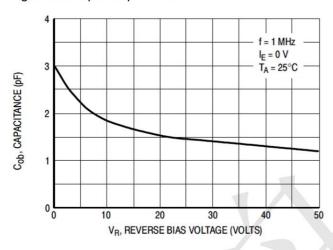


Figure 11. Input Voltage vs. Output Current

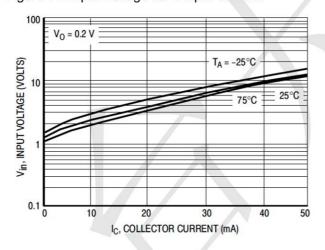


Figure 8. DC Current Gain

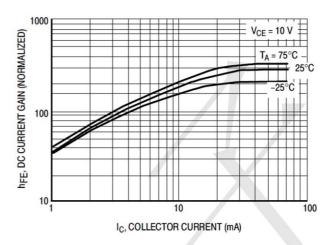
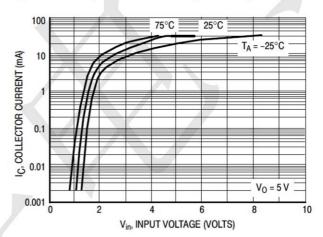


Figure 10. Output Current vs. Input Voltage





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DTC144EM

Figure 12. V_{CE(sat)} vs. I_C

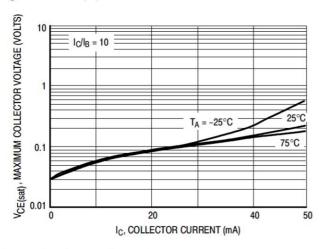


Figure 14. Output Capacitance

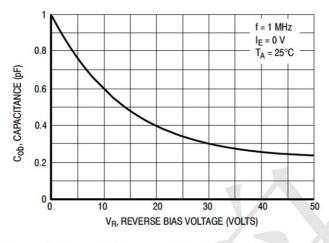


Figure 16. Input Voltage vs. Output Current

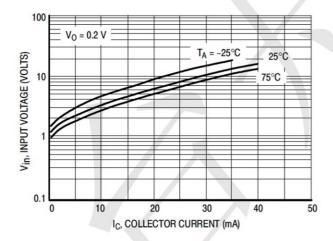


Figure 13. DC Current Gain

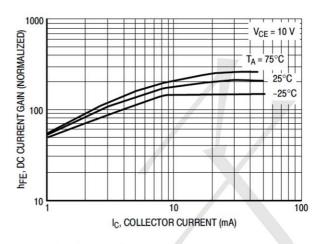
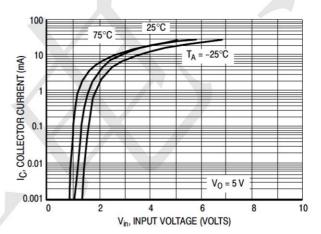


Figure 15. Output Current vs. Input Voltage





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DTC114YM

Figure 17. V_{CE(sat)} vs. I_C

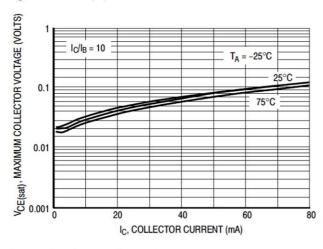


Figure 19. Output Capacitance

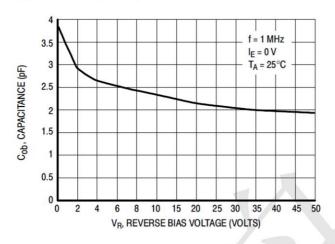


Figure 21. Input Voltage vs. Output Current

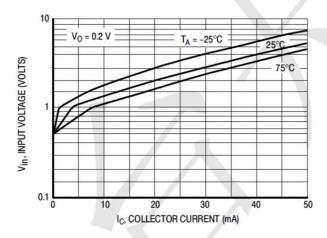


Figure 18. DC Current Gain

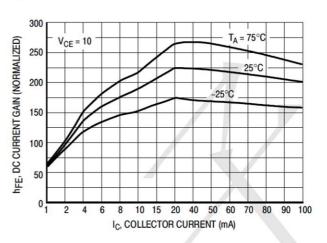
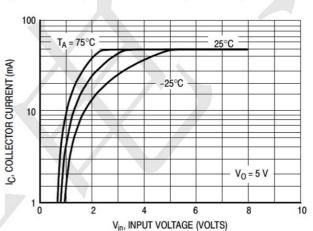


Figure 20. Output Current vs. Input Voltage





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DTC143ZM

Figure 22. V_{CE(sat)} versus I_C

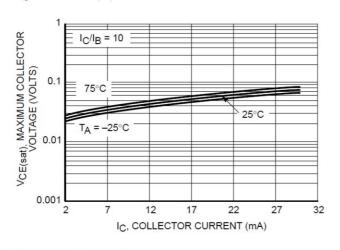


Figure 24. Output Capacitance

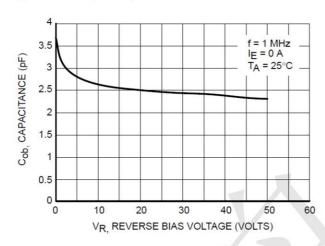


Figure 26. Input Voltage vs. Output Current

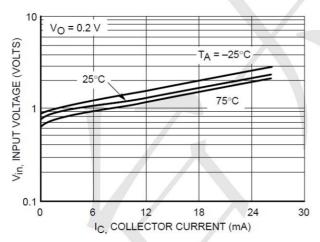


Figure 23. DC Current Gain

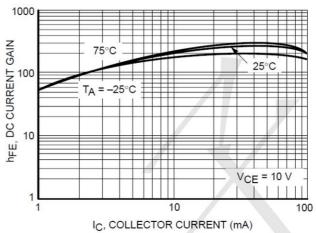
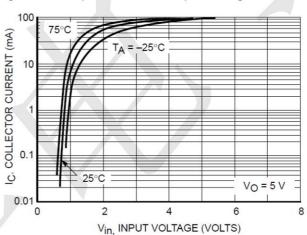


Figure 25. Output Current vs. Input Voltage





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TYPICAL APPLICATIONS FOR NPN BRTs

Figure 27. Level Shifter: Connects 12 or 24 Volt Circuits to Logic

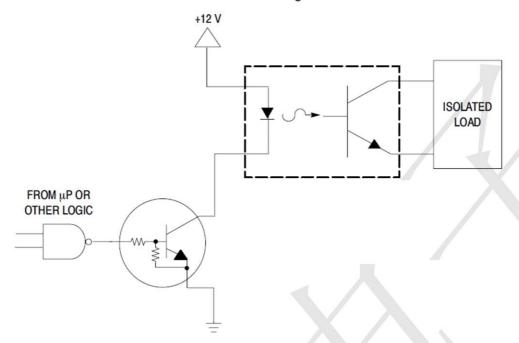
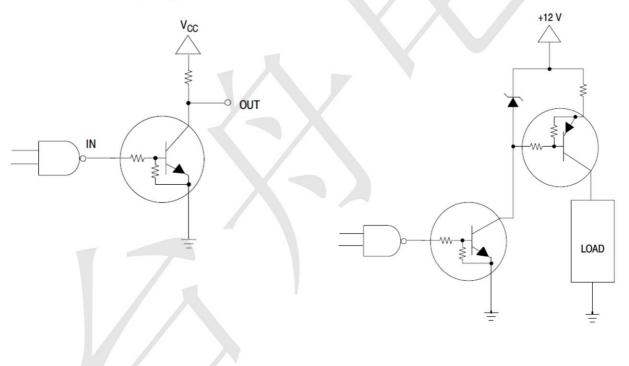


Figure 28. Open Collector Inverter:

Inverts the Input Signal

Figure 29. Inexpensive, Unregulated Current Source



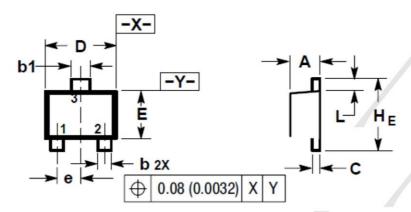


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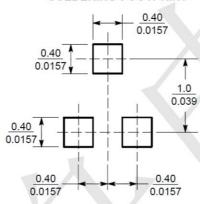
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PACKAGE INFORMATION

Dimension in SOT-723 (Unit: mm)



SOLDERING FOOTPRINT



1	mm
1	inches

DIM	MILLIM	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.45	0.55	0.018	0.022	
b	0.15	0.27	0.0059	0.0106	
b1	0.25	0.35	0.010	0.014	
С	0.07	0.17	0.0028	0.0067	
D	1.15	1.25	0.045	0.049	
E	0.75	0.85	0.03	0.034	
е	0.40	BSC	0.016 BSC		
HE	1.15	1.25	0.045	0.049	
L	0.15	0.25	0.0059	0.0098	

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DTC115TKAT146 DTC124TETL DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA123EF3T5G

NSBA143TF3T5G NSBA144TF3T5G NSBC113EF3T5G NSBC124XF3T5G SMUN5330DW1T1G SSVMUN5312DW1T2G

RN1303(TE85L,F) RN1306(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79 EMH15T2R SMUN2214T3G SMUN5335DW1T1G

NSBC143ZPDP6T5G NSVDTA143ZET1G NSVDTC143ZET1G NSVMUN5113DW1T3G SMUN2214T1G FMA7AT148 DTC114EUA-TP

SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP

DTA113EM3T5G DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G NSVDTC143ZM3T5G SMUN5335DW1T2G

SMUN5216DW1T1G NSVMUN5316DW1T1G NSVMUN5215DW1T1G